

# isc N-Channel MOSFET Transistor

# FQA24N50F

### • FEATURES

- With TO-3PN packaging
- High speed switching
- Very high commutation ruggedness
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operationz

### • APPLICATIONS

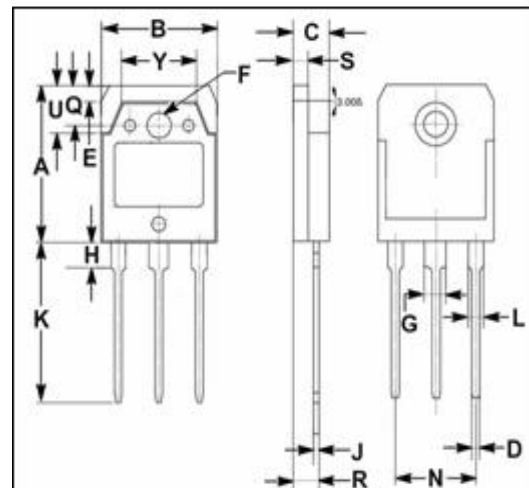
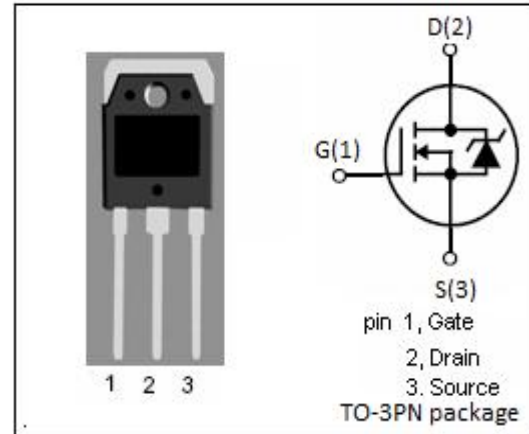
- Switching applications

### • ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	500	V
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-Continuous@ $T_c=25^{\circ}\text{C}$ $T_c=100^{\circ}\text{C}$	24 15.2	A
$I_{DM}$	Drain Current-Single Pulsed	96	A
$P_D$	Total Dissipation	290	W
$T_j$	Operating Junction Temperature	-55~150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^{\circ}\text{C}$

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.43	$^{\circ}\text{C}/\text{W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	40	$^{\circ}\text{C}/\text{W}$



DIM	mm	
	MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

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## ELECTRICAL CHARACTERISTICS

T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA	500			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =±30V; I <sub>D</sub> =0.25mA	3		5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =12A		590	650	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±30V; V <sub>DS</sub> = 0V			±0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 500V; V <sub>GS</sub> = 0V; T <sub>J</sub> =25°C V <sub>DS</sub> = 400V; V <sub>GS</sub> = 0V; T <sub>J</sub> =125°C			50 500	μA
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =24A, V <sub>GS</sub> = 0 V			1.4	V

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